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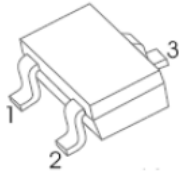
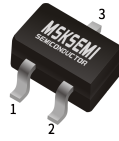


GDT



PLED

Product data sheet


 1. BASE
 2. EMITTER
 3. COLLECTOR

SOT-323
SS8550W TRANSISTOR (PNP)

FEATURES

- High Collector Current
- Complementary to SS8050W

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current	-1.5	A
P _c	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	167	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

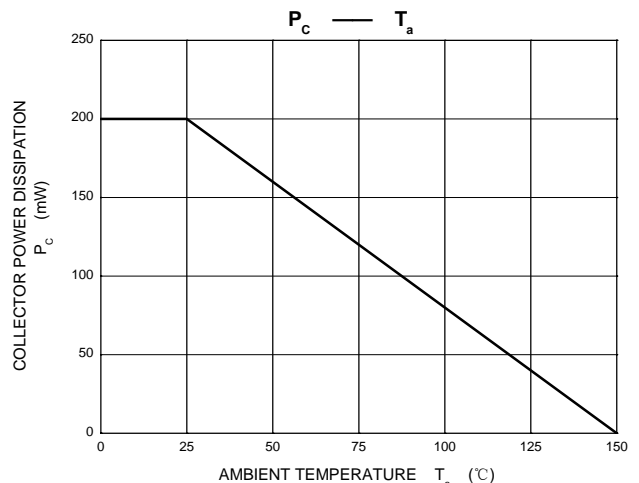
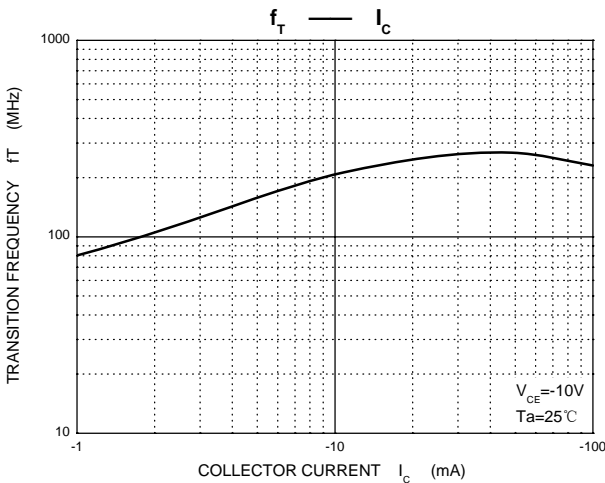
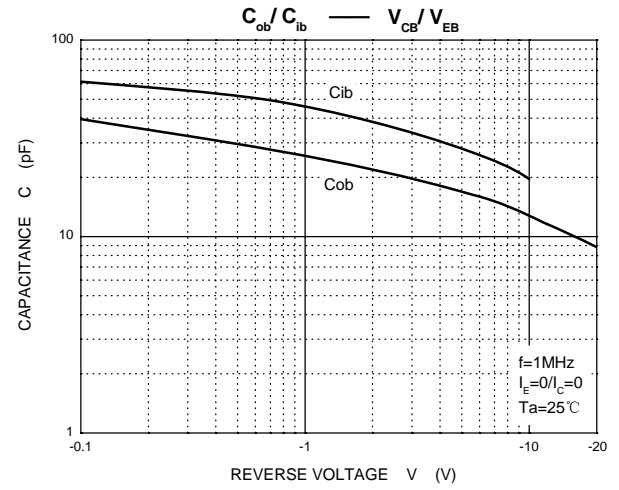
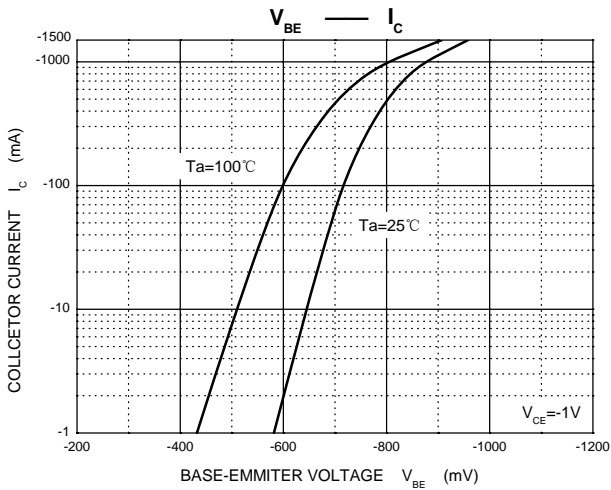
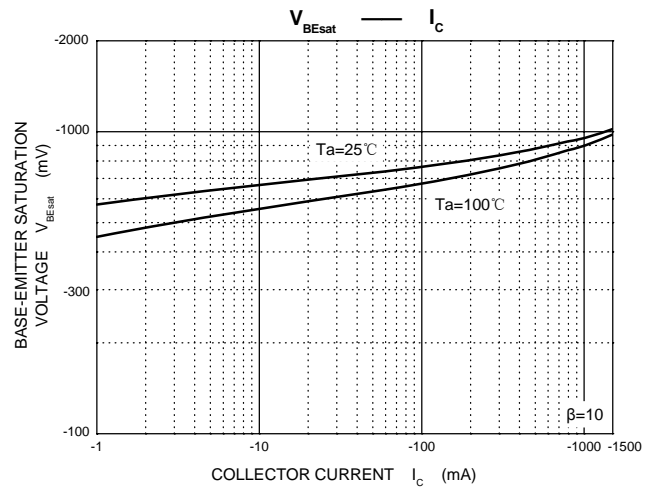
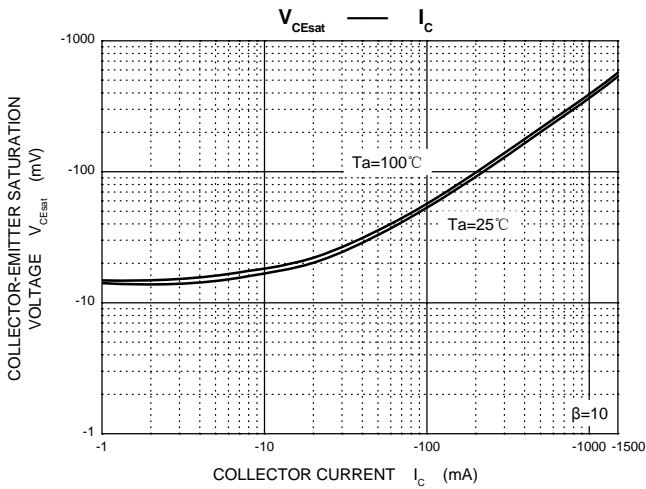
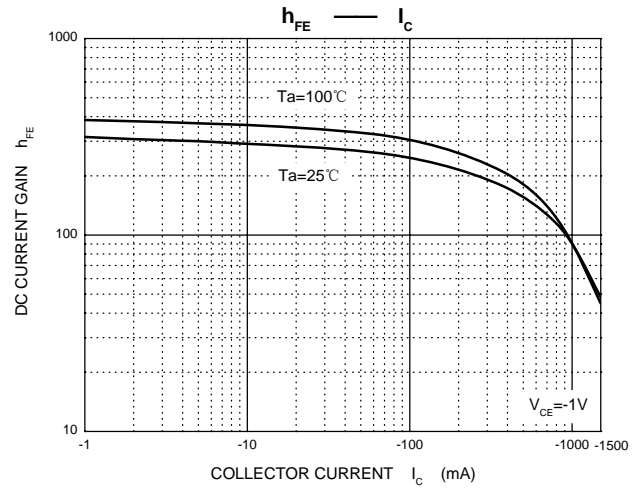
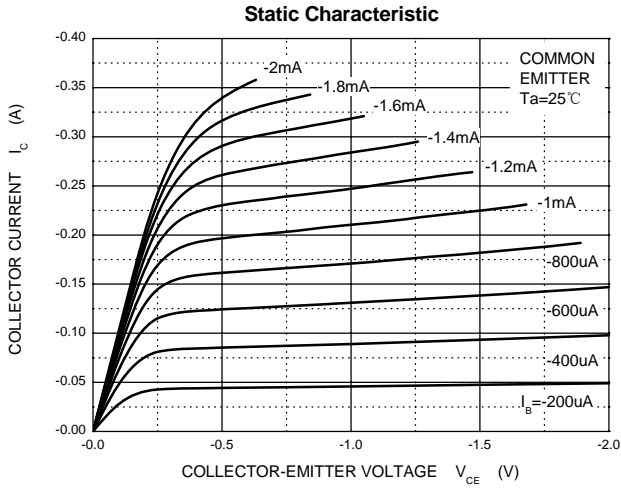
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-0.1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-20V, I _B =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	120		400	
	h _{FE(2)}	V _{CE} =-1V, I _C =-800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA			-1.2	V
Base-emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=30MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			20	pF

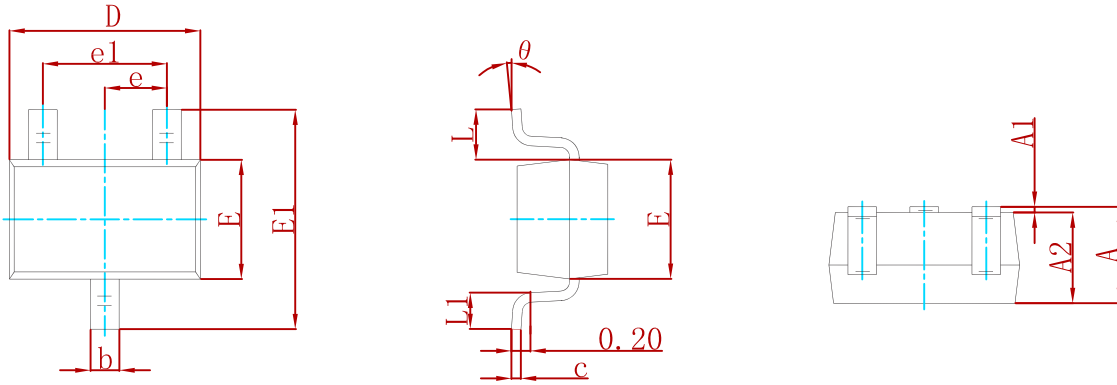
CLASSIFICATION OF h_{FE(1)}

RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400
MARKING	Y2		

Typical Characteristics

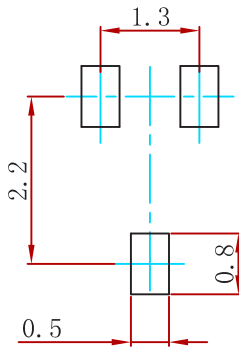


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SS8550W	SOT-323	3000

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